**What is claimed is:**

1. A method for manufacturing a semiconductor laser device, comprising the steps of:

forming an electrode pattern on an upper surface of a semiconductor wafer stacked at least a light emission layer;

cutting the resultant semiconductor wafer for predetermined width to yield a plurality of semiconductor bars; and

sectioning the semiconductor bars into a desired size to form semiconductor laser devices having a pair of cleavage surfaces which are parallel to a chip-width direction and distant from each other by a predetermined resonator length,

wherein the electrode pattern formed in the step of forming an electrode pattern is continuous at least in a resonator-length direction.

2. The method of claim 1, wherein a plurality of electrode patterns are formed in a plurality of rows at a fixed row pitch in a chip-width direction with a plurality of markers in a predetermined shape being formed at a pitch not greater than a resonator length at one or both of the edges of the electrode patterns extending in the resonator-length direction.

3. The method of claim 1, wherein the electrode pattern is formed on the substantially entire surface of the

semiconductor wafer with a plurality of openings to be markers being formed on hypothetical lines sectioning the electrode pattern at intervals each of a chip width and at a pitch not greater than a resonator length in a resonator-length direction.

4. The method of claim 1, wherein the electrode pattern is formed on the substantially entire surface of the semiconductor wafer with a plurality of markers being formed at corresponding positions of laser light emitting channels of the electrode pattern in the chip-width direction at a pitch equal to a chip width in a chip-width direction and at a pitch not greater than a resonator length in the resonator-length direction of the electrode pattern.

5. A semiconductor laser device, comprising:

a semiconductor layer portion which includes at least a light emission layer and has a pair of cleavage surfaces which are parallel to a chip-width direction and distant from each other by a predetermined resonator length; and

an electrode pattern piece formed on an upper surface of the semiconductor layer portion,

wherein the electrode pattern piece comes in contact with the pair of cleavage planes at both of the edges of the electrode pattern piece extending in a chip-width direction.

6. The device of claim 5, wherein the electrode pattern piece has a marker or makers in a predetermined shape at one or both of the edges of the electrode pattern piece extending in a resonator-length direction.

7. The device of claim 6, wherein the markers at both of the respective edges of the electrode pattern piece extending in the resonator-length direction are symmetric with respect to a center line of the electrode pattern piece extending in the resonator-length direction and asymmetric with respect to a hypothetical line of the electrode pattern piece extending in the chip-width direction bisectioning the overall length of the marker.

8. The device of claim 6 or 7, wherein a plurality of markers are formed at a fixed pitch with the overall lengths of the plurality of markers in the resonator-length direction each being set to be equal to L/n, wherein L is a resonator length and n is an integer not smaller than one, and being set to be equal to the pitch of the markers.

9. The device of claim 5, the electrode pattern piece has a marker at a corresponding position of a laser light emitting channel.

10. The device of any one of claims 6 to 9, wherein the marker is set so that the ratio of its overall length in the resonator-length direction to its maximum length in the chip-width direction is 1:5 to 5:1.